



SINGLE SLEW RATE CONTROLLED LOAD SWITCH

## Description

The AP22913 slew rate controlled load switch is a single P-channel MOSFET power switch designed for high-side load-switching applications. The MOSFET has a typical  $R_{DS(on)}$  of 54m $\Omega$  at 5V (X1-WLB0909-4), allowing increased load current handling capacity with a low forward voltage drop. The turn-on slew rate of the device is controlled internally. V<sub>IN</sub> and V<sub>OUT</sub> are isolated during the OFF state with a TRCB (True Reverse Current Blocking) feature.

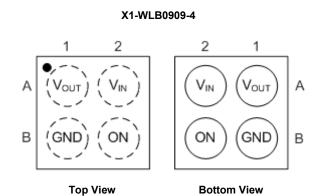
The AP22913 load switch is designed to operate from 1.4V to 5.5V, making it ideal for 1.8V, 2.5V, 3.3V, and 5V systems. The typical quiescent supply current is only  $1\mu$ A.

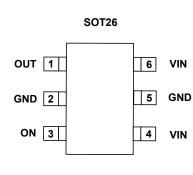
The AP22913 is available in the wafer level chip scale 4-pin, X1-WLB0909-4 0.5mm pitch and standard SOT26 package.

#### Features

- Wide Input Voltage Range: 1.4V to 5.5V
- Low On-Resistance (X1-WLB0909-4):
  - 92mΩ Typical @1.5V
  - 76mΩ Typical @1.8V
  - 56mΩ Typical @3.3V
  - 54mΩ Typical @5.0V
- High DC Current Capability up to 2A
- Truly Reverse Current Block (TRCB)
- Discharging Resistor on V<sub>OUT</sub> When Disabled
- Ultra-Low Quiescent Current 1µA
- Active-High Control Pin
  - Minimum 1.1V V<sub>IH</sub> of ON
- ESD Protection:
  - Human Body Model: 2kV
  - Charged Device Model: 1kV
- Package:
  - SX1-WLB0909-4 with Backside Laminate
  - Standard Green SOT26
  - 0.9mm x 0.9mm, 0.5mm Ball Pitch
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

## **Pin Assignments**





Top View

#### Applications

- Mobile Device and Smart Phones
- Portable Media Devices
- Wearable Devices
- Advanced Notebooks, UMPC and MID
- Portable Medical Devices
- GPS and Navigation Equipment

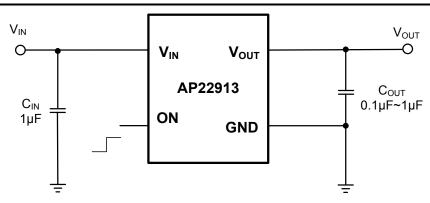
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

<sup>2.</sup> See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.



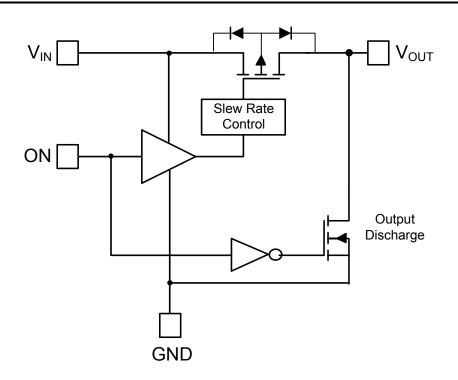
## **Typical Applications Circuit**



# **Pin Descriptions**

Pin Name	Pin Number WLCSP	Function	
V <sub>OUT</sub>	A1	Voltage output pin. This is the pin to the P-channel MOSFET drain connection. Bypass to ground through a $0.1\mu$ F or $1\mu$ F capacitor.	
V <sub>IN</sub>	A2	Voltage input pin. This is the pin to the P-channel MOSFET source. Bypass to ground through a 1µF capacitor.	
GND	B1	Ground.	
ON	B2	Enable input, active high	

# **Functional Block Diagram**





Symbol	Parameter	Ratii	Ratings	
ESD HBM	Human Body Model ESD Protection	6		kV
ESD CDM	Charged Device Model ESD Protection	2		kV
V <sub>IN</sub>	Input Voltage	-0.3	to 6	V
V <sub>OUT</sub>	Output Voltage	-0.3	to 6	V
V <sub>ON</sub>	ON Voltage	-0.3	to 6	V
I <sub>LOAD</sub>	Maximum Continuous Load Current	2	2	
I <sub>LOAD</sub>	Maximum Pulse Load Current, Pulse <300µs, 2% Duty Cycle	2.	2.5	
TJ	Maximum Junction Temperature	+12	+125	
T <sub>ST</sub>	Storage Temperature Range	-65 to	-65 to +150	
PD	Power Dissipation	WLB0909-4	930	mW
١D		SOT-26	760	
R <sub>0JA</sub>	Thermal Resistance, Junction to Ambient (Note 4)	WLB0909-4	136	°C/W
• <b>∿</b> ⊎JA		SOT-26	165	
R <sub>θJC</sub>	Thermal Resistance, Junction to Case (Note 5)	WLB0909-4	31	°C/W
<b>N</b> ØJC		SOT-26	30	

## Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Notes: 4. The JEDEC high-K (2s2p) board used to derive this data was a 3 inch x 3 inch, multilayer board with 1oz internal power and ground planes with2oz copper traces on top and bottom of the board.

5. Thermal resistance from junction to case.

Caution: Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

## Recommended Operating Conditions (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Pa	arameter	Min	Мах	Unit
VIN	Input Voltage		1.4	5.5	V
V <sub>ON</sub>	ON Voltage Range	ON Voltage Range		5.5	V
V <sub>OUT</sub>	Output Voltage		1.4	5.5	V
I <sub>OUT</sub>	Output Current		0	2.0	А
VIH	ON High-Level Input Vol	ON High-Level Input Voltage		5.5	V
N/	ON Low-Level Input	V <sub>IN</sub> = 3.6V to 5.5V	0	0.6	V
VIL	V <sub>IL</sub> Voltage	V <sub>IN</sub> = 1.4V to 3.6V	0	0.4	V
TA	Operating Ambient Temperature		-40	+85	°C



# **Electrical Characteristics** ( $T_A = -40^{\circ}C$ to $+85^{\circ}C$ , $V_{IN} = 1.4$ to 5.5V, $V_{ON} = V_{IN}$ (Enabled), $V_{ON} = 0V$ (Disabled), $C_{IN} = 1\mu$ F, $C_{OUT} = 0.1\mu$ F, unless otherwise specified.) (Note 6)

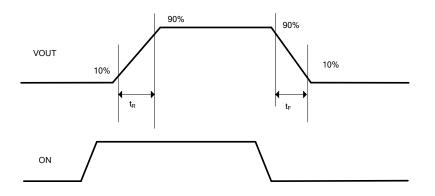
Symbol	Parameters	Test Cor	nditions	Min	Тур	Max	Unit
			V <sub>IN</sub> = 5.25V	_	1.4	7	
	Input Quiescent Current		V <sub>IN</sub> = 4.2V	_	1	5	
lq		I <sub>OUT</sub> = 0mA,	V <sub>IN</sub> = 3.6V	_	0.7	5	μA
·œ		V <sub>ON</sub> = Enabled	$V_{IN} = 2.5V$	_	0.5	3.5	
			$V_{IN} = 1.5V$	<u> </u>	0.3	3.5	
			V <sub>IN</sub> = 5.25V	_	0.0	1	
				-			
		$R_L = 1M\Omega$ ,	$V_{IN} = 4.2V$		0.1	1	
I <sub>SHDN</sub>	Input Shutdown Current	V <sub>ON</sub> = Disabled	$V_{IN} = 3.6V$	_	0.1	1	μA
			V <sub>IN</sub> = 2.5V	—	0.1	1	
			V <sub>IN</sub> = 1.5V	—	0.1	1	
			V <sub>IN</sub> = 5.25V	—	0.1	2	
	$\lambda = -0 \lambda$	$V_{IN} = 4.2V$	—	0.1	2		
I <sub>IN_LEAK</sub>	Input Leakage Current	$V_{OUT} = 0V,$	V <sub>IN</sub> = 3.6V	—	0.1	2	μA
	V <sub>ON</sub> = Disabled	V <sub>IN</sub> = 2.5V	_	0.1	2		
			V <sub>IN</sub> = 1.5V	_	0.1	2	
			+25°C	<u> </u>	54	70	
		V <sub>IN</sub> = 5.0V	Full	<u> </u>	_	95	
			+25°C	_	55	70	
		V <sub>IN</sub> = 4.2V	Full	_	_	95	
			+25°C	_	56	80	
	Switch On-resistance, I <sub>OUT</sub> = -200mA at	V <sub>IN</sub> = 3.3V	Full	_	_	95	- mΩ
	X1-WLB0909-4 package	V <sub>IN</sub> = 2.5V	+25°C	_	60	85	
			Full	—	—	115	
		(-1.0)/	+25°C	—	76	100	
	V <sub>IN</sub> = 1.8V	Full	_	—	130	1	
			+25°C	—	92	120	-
-		V <sub>IN</sub> = 1.5V	Full	_	—	150	
R <sub>DS(on)</sub>			25°C	—	84	100	
		V <sub>IN</sub> = 5.0V	Full	—	—	125	
		$\lambda (m = 4.0)$	25°C	_	85	100	1
		V <sub>IN</sub> = 4.2V	Full	—	—	125	
		1/ = 2.21/	25°C	—	86	100	- mΩ
	Switch On-resistance, I <sub>OUT</sub> = -200mA at	V <sub>IN</sub> = 3.3V	Full	_	—	125	
	SOT26 package	V <sub>IN</sub> = 2.5V	25°C	—	90	115	
		VIN - 2.3V	Full	—		145	
		V <sub>IN</sub> = 1.8V	25°C		106	130	-
		VIN - 1.0V	Full	—	—	160	
		V <sub>IN</sub> = 1.5V	25°C	—	122	150	
		VIN - 1.5V	Full	—	—	180	
R <sub>DIS</sub>	Discharge FET On-resistance	V <sub>IN</sub> = 3.3V, V <sub>ON</sub> = 0V, I <sub>OUT</sub> = 30mA, T <sub>A</sub> = +25°C		—	150	200	Ω
10.4.0		V <sub>IN</sub> increasing		—	—	1.2	
UVLO	Undervoltage Lockout	V <sub>IN</sub> decreasing		0.5	1 _	_	V
VT_RCB	TRCB Trigger Point	Vout - Vin			44	_	mV
VR_RCB	TRCB Release Point			_	0	_	mV
	TRCB Response Time	VIN - VOUT		-	10		
t <sub>т_RCB</sub>		$V_{IN} = 5V, V_{ON} = V_{IN}$			10		μs
I <sub>RCB</sub>	TRCB Reverse Leakage Current (Current from V <sub>IN</sub> )	$V_{OUT} - V_{IN} > V_{T_{RCB}}, V_{ON} = Enabled$ $V_{IN} = 0V, V_{OUT} = 5.5V, V_{ON} = Disabled$			0.3	-	μA
I <sub>ON</sub>	ON Input Leakage	$V_{ON} = 0V, 5.25V \text{ or } V_{ON} = V_{IN}$			_	1	μA

Note: 6. Specifications are over -40°C to +85°C and are guaranteed by characterization and design.

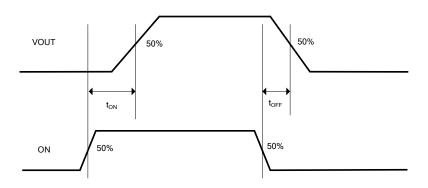


## Timing Characteristics (Note 7)

Symbol	Parameters	Test Conditions	Min	Тур	Мах	Unit
t <sub>ON</sub>	Output Turn-on Time		—	720	—	μs
t <sub>OFF</sub>	Output Turn-off Time		—	5	—	μs
t <sub>R</sub>	Output Rise Time	$V_{IN} = 5V, R_L = 10\Omega, C_{OUT} = 0.1\mu F$	_	660	—	μs
t <sub>F</sub>	Output Fall Time		—	2.5	—	μs
ton	Output Turn-on Time		_	1050	_	μs
t <sub>OFF</sub>	Output Turn-off Time		—	6.5	—	μs
t <sub>R</sub>	Output Rise Time	$V_{\rm IN} = 3.3 V, R_{\rm L} = 10 \Omega, C_{\rm OUT} = 0.1 \mu F$	_	770	_	μs
t <sub>F</sub>	Output Fall Time		—	3.0	—	μs
ton	Output Turn-on Time		_	2300	_	μs
toff	Output Turn-off Time	N/ 45/ D 400.0 04/5	—	18	_	μs
t <sub>R</sub>	Output Rise Time	$V_{IN} = 1.5V, R_L = 10\Omega, C_{OUT} = 0.1\mu F$	—	1400	—	μs
t <sub>F</sub>	Output Fall Time		—	5.0	_	μs



Output Rise ( $t_R$ ) and Fall ( $t_F$ ) Time

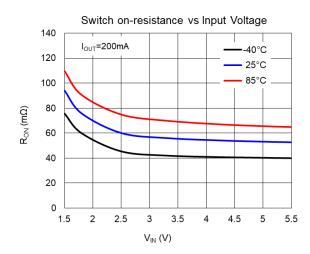


Output Turn On (t\_on) and Turn Off (t\_off) Time

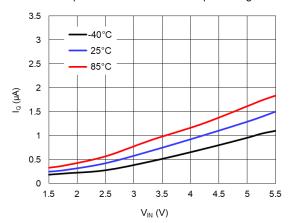
Note: 7. Rise and fall time of the control signal are less than 100ns.



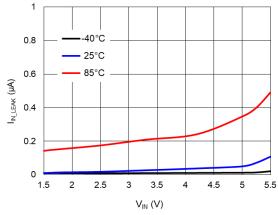
# Typical Performance Characteristics (C<sub>IN</sub> = 1µF, C<sub>OUT</sub> = 0.1µF, unless otherwise specified.)



Input Quiescent Current vs Input Voltage

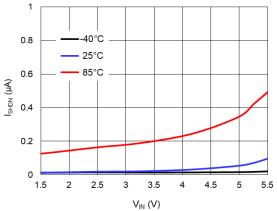




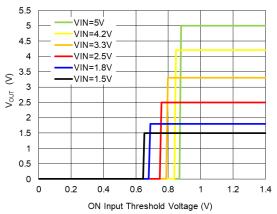


Switch on-resistance vs Temperature 180 I<sub>OUT</sub>=200mA 1.5<sup>'</sup>V 160 1.8V 2.5V 140 3.3V 4.2V 120 5V 5.5V 100  $R_{ON}$  (m $\Omega$ ) 80 60 40 20 0 -40 -15 10 35 60 85 Temperature (°C)

Input Shutdown Current vs Input Voltage

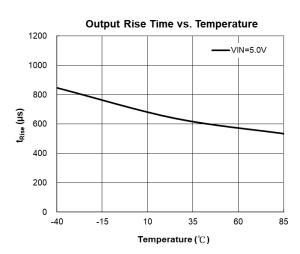


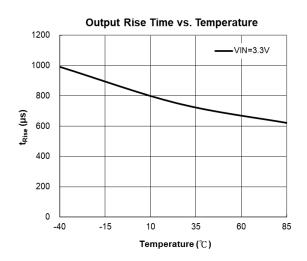
ON Input Threshold Voltage (High Active)



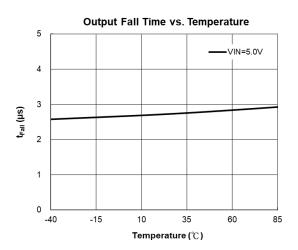


# **Typical Performance Characteristics** (continued) ( $C_{IN} = 1\mu F$ , $C_{OUT} = 0.1\mu F$ , $R_L = 10\Omega$ , unless otherwise specified.)

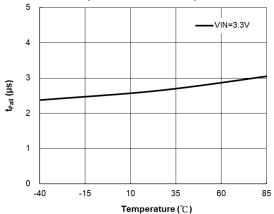


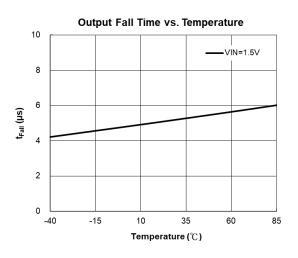


Output Rise Time vs. Temperature 3000 VIN=1.5V 2500 2000 t<sub>Rise</sub> (Jus) 1200 1000 500 0 -40 -15 10 35 60 85 Temperature (°C)



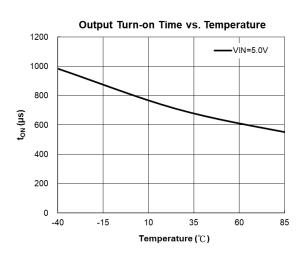
Output Fall Time vs. Temperature

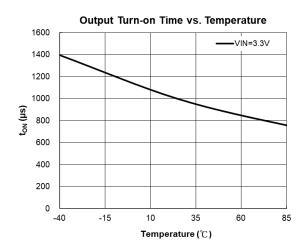




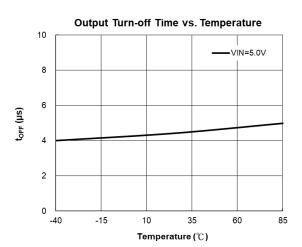


# **Typical Performance Characteristics** (continued) ( $C_{IN} = 1\mu F$ , $C_{OUT} = 0.1\mu F$ , $R_L = 10\Omega$ , unless otherwise specified.)





Output Turn-on Time vs. Temperature 4000 -VIN=1.5V 3500 3000 2500 t<sub>on</sub> (µs) 2000 1500 1000 500 0 -40 -15 35 60 85 10 Temperature (°C)



Output Turn-off Time vs. Temperature

10

35

Temperature (℃)

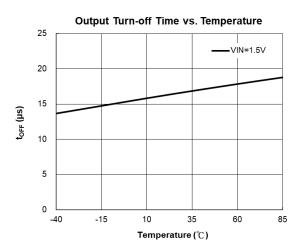
60

85

0

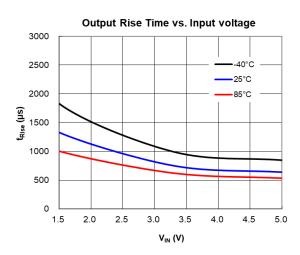
-40

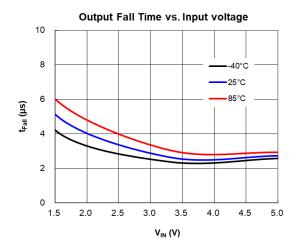
-15

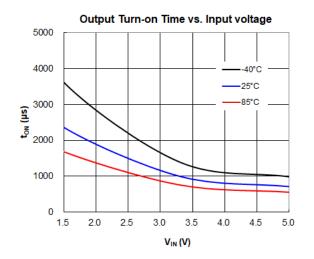




# **Typical Performance Characteristics** (continued) ( $C_{IN} = 1\mu F$ , $C_{OUT} = 0.1\mu F$ , $R_L = 10\Omega$ , unless otherwise specified.)



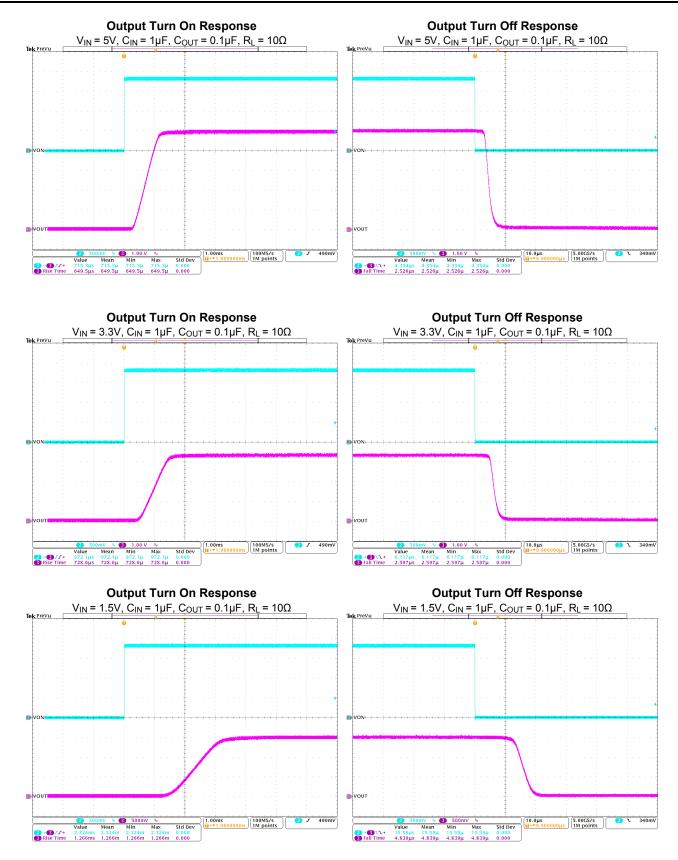




Output Turn-off Time vs. Input voltage 25 20 -40°C 25°C 85°C 15 t<sub>oFF</sub> (µs) 10 5 0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 V<sub>IN</sub> (V)

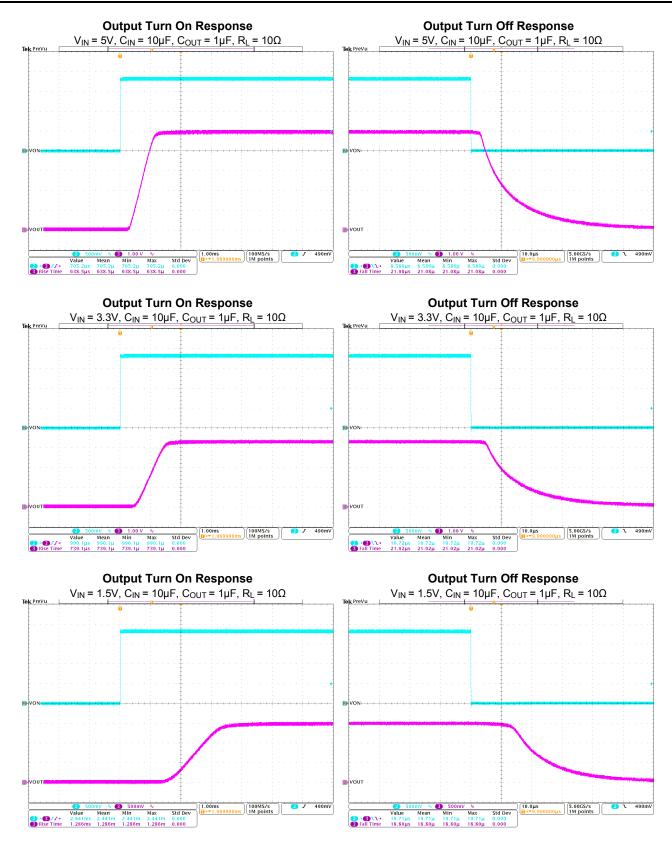


## **Typical Performance Characteristics** (continued) (T<sub>A</sub> = +25°C, V<sub>ON</sub> = 1.8V, unless otherwise specified.)



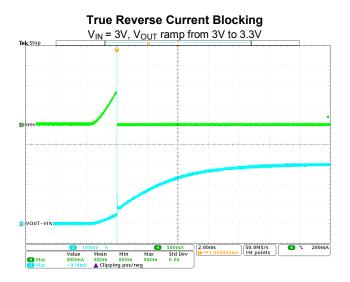


## **Typical Performance Characteristics** (continued) (T<sub>A</sub> = +25°C, V<sub>ON</sub> = 1.8V, unless otherwise specified.)





# Typical Performance Characteristics (continued) (T<sub>A</sub> = +25°C, C<sub>IN</sub> = 1µF, C<sub>OUT</sub> = 0.1µF, unless otherwise specified.)





## **Application Information**

#### Input Capacitor

A 1 $\mu$ F capacitor is recommended to connect between the V<sub>IN</sub> and GND pins to decouple glitch and noise of the input power supply. The input capacitor has no specific type or ESR (Equivalent Series Resistance) requirement. However, for higher current application, ceramic capacitors are recommended due to their capability to withstand input current surges from low impedance sources, such as batteries in portable applications. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both V<sub>IN</sub> and GND.

#### **Output Capacitor**

The  $0.1\mu$ F to  $1\mu$ F capacitor is recommended to connect between the V<sub>OUT</sub> and GND pins to stabilize and accommodate load transient condition. The output capacitor has no specific type or ESR requirement. The amount of the capacitance may be increased without limit. For PCB layout, the output capacitor must be placed as close as possible to V<sub>OUT</sub> and GND pins. The traces must be kept as short as possible.

#### **Enable/Shutdown Operation**

The AP22913 is turned on by setting the ON pin high, and is turned off by pulling it low. To ensure proper operation, the signal source used to drive the ON pin must be able to swing above and below the specified turn-on/off voltage thresholds listed in the Electrical Characteristics section under  $V_{IL}$  and  $V_{IH}$ .

#### True Reverse Current Blocking

An internal reverse voltage comparator disables the power-switch when the output voltage ( $V_{OUT}$ ) is driven higher than the input voltage ( $V_{IN}$ ), by  $V_{T\_RCB}$ , to quickly (10µs typ) stop the flow of current towards the input side of the switch.

Reverse current protection is always active, even when the power switch is disabled. Additionally, undervoltage lockout (UVLO) protection turns the switch off if the input voltage is too low.

#### **Discharge Operation**

The AP22913 offers a discharge option that helps to discharge the output charge when disabled.

#### **Power Dissipation**

The maximum IC junction temperature should be restricted to +125°C under normal operating conditions. The device power dissipation and proper sizing of the thermal plane is critical to avoid thermal shutdown and ensure reliable operation. Power dissipation of the device depends on input voltage and load conditions and can be calculated by:

$$P_{\rm D} = I_{\rm OUT}^2 x R_{\rm DSON}$$
 (1)

However, the maximum power dissipation that can be handled by the device depends on the maximum junction to ambient thermal resistance, maximum ambient temperature, and maximum device junction temperature, which can be approximated by the equation below:

$$P_{D(MAX)} = \frac{(125^{\circ}C - T_A)}{\theta_{JA}}$$
(2)

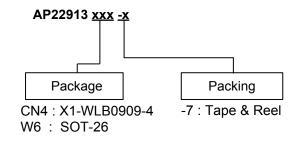
#### Layout Guidelines

Good PCB layout is important for improving the thermal performance of the device. All trace lengths should be kept as short as possible. The input  $(V_{IN})$  and output  $(V_{OUT})$  PCB traces should be as wide as possible to reduce stray impedance.

Use a ground plane to enhance the power dissipation capability of the device if applicable. Place input and output capacitors close to the device to minimize the effects of parasitic inductance.



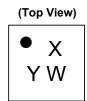
## **Ordering Information**



Part Number	Package Code	Packaging	7" Tape a	and Reel
Fait Nulliber	Fackage Code	Packaging	Quantity	Part Number Suffix
AP22913CN4-7	CN4	X1-WLB0909-4	3,000/Tape & Reel	-7
AP22913W6-7	W6	SOT26	3,000/Tape & Reel	-7

## **Marking Information**

(1) X1-WLB0909-4



X : Identification Code
Y : Year : 0~9
W : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week

Part Number	Package	Identification Code
AP22913CN4-7	X1-WLB0909-4	Ē

#### (2) SOT-26

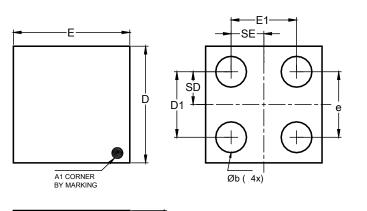
( Top View )	
6 5 4	XX : Identification Code
XXYWX	Y : Year 0∼9 W : Week : A∼Z : 1∼26 week; a∼z : 27∼52 week; z represents
•	52 and 53 week X : Internal Code

Part Number	Package	Identification Code
AP22913W6-7	SOT26	N9



## **Package Outline Dimensions**

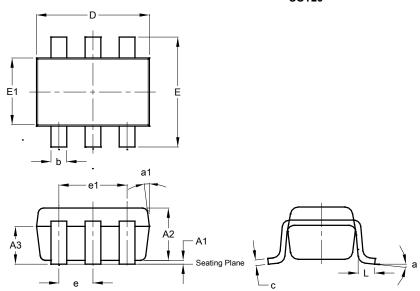
Please see http://www.diodes.com/package-outlines.html for the latest version.



A2

SEATING PLANE

	X1-WLB0909-4							
Dim	Min	Max	Тур					
Α	0.410	0.500	0.455					
A1	0.160	0.200	0.180					
A2	0.225	0.275	0.250					
b	0.215	0.255	0.235					
D	0.840	0.900	0.870					
D1	0.450	0.550	0.500					
E	0.840	0.900	0.870					
E1	0.450	0.550	0.500					
е	0	.500 BS	С					
SD	0.250 BSC							
SE	0.250 BSC							
All	Dimens	ions in	mm					



SOT26						
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
A3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
C	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	-	-	0.95			
e1	-	-	1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а	-	-	8°			
a1	-	-	7°			
All	Dimen	sions	in mm			

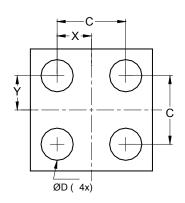
SOT26

X1-WLB0909-4



# **Suggested Pad Layout**

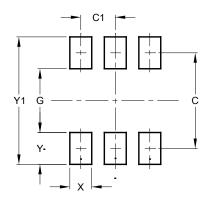
Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.500
D	0.235
Х	0.250
Y	0.250

SOT26

X1-WLB0909-4



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



AP22913

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